

NOT RECOMMENDED FOR NEW DESIGN CONTACT US



PAM2312

1A STEP-DOWN DC-DC CONVERTER

Description

The PAM2312 is a step-down current-mode, DC-DC converter. At heavy load, the constant frequency PWM control performs excellent stability and transient response. To ensure the longest battery life in portable applications, the PAM2312 provides a power-saving Pulse- Skipping Modulation (PSM) mode to reduce quiescent current under light load operation to save power.

The PAM2312 supports a range of input voltages from 2.5V to 5.5V, allowing the use of a single Li+/Li-polymer cell, multiple Alkaline/NiMH cell, USB, and other standard power sources. The output voltage is adjustable from 0.6V to the input voltage. All versions employ internal power switch and synchronous rectifier to minimize external part count and realize high efficiency. During shutdown, the input is disconnected from the output and the shutdown current is less than $1\mu A$. Other key features include under-voltage lockout to prevent deep battery discharge.

The PAM2312 is available in TSOT25 packages.

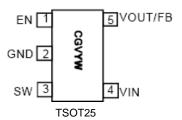
Features

- Efficiency up to 96%
- Only 40µA (typ.) Quiescent Current
- Output Current: Up to 1A
- Internal Synchronous Rectifier
- 1.5MHz Switching Frequency
- Soft Start
- Under-Voltage Lockout
- Short Circuit Protection
- Thermal Shutdown
- TSOT25 Packages
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Pin Assignments

Top View



Applications

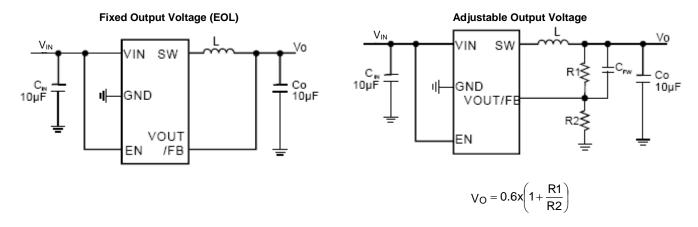
- Cellular Phone
- Portable Electronics
- Wireless Devices
- Cordless Phone
- Computer Peripherals
- Battery Powered Widgets
- Electronic Scales
- Digital Frame

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



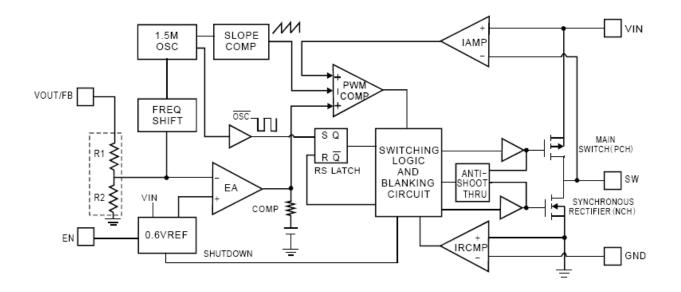
Typical Applications Circuit



Pin Descriptions

Pin	TSOT25	Function
Number	Pin Name	Function
4	VIN	Chip Main Power Supply Pin
2	GND	Ground
1	EN	Enable Control Input. Force this pin voltage above 1.5V, enables the chip, and below 0.3V shuts down the device.
5	VOUT/FB	VOUT: Output voltage feedback pin, an internal resistive divider divides the output voltage down for comparison to the internal reference voltage. FB: Feedback voltage to internal error amplifier, the threshold voltage is 0.6V.
3	SW	The drains of the internal main and synchronous power MOSFET.

Functional Block Diagram





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

These are stress ratings only and functional operation is not implied. Exposure to absolute maximum ratings for prolonged time periods may affect device reliability. All voltages are with respect to ground.

Parameter	Rating	Unit
Input Voltage	-0.3 to +6.0	V
EN, FB Pin Voltage	-0.3 to V _{IN}	V
SW Pin Voltage	-0.3 to (V _{IN} +0.3)	V
Junction Temperature	+150	°C
Storage Temperature Range	-65 to +150	°C
Soldering Temperature	+300, 5s	°C

Recommended Operating Conditions (@T_A = +25°C, unless otherwise specified.)

Parameter	Rating	Unit
Supply Voltage	2.5 to 5.5	V
Operation Temperature Range	-40 to +85	٠ć
Junction Temperature Range	-40 to +125	

Thermal Information

Symbol	Parameter	Package	Max	Unit
θјс	Thermal Resistance (Junction to Case)	TSOT25 (Note 4)	130	°C/W
θја	Thermal Resistance (Junction to Ambient)	TSOT25	250	C/VV
PD	Internal Power Dissipation	TSOT25	400	mW

Note: 4. The maximum output current for TSOT25 package is limited by internal power dissipation capacity as described in Application Information herein after.

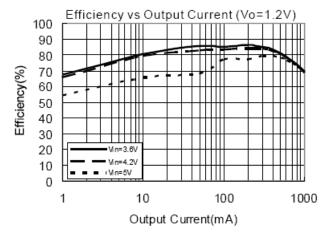


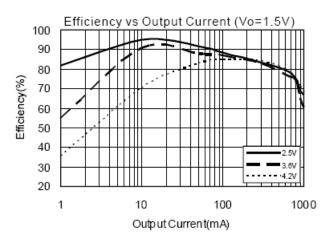
$\textbf{Electrical Characteristics} \ (@T_A = +25^{\circ}C,\ V_{IN} = 3.6V,\ V_O = 1.8V,\ C_{IN} = 10\mu\text{F},\ C_{OUT} = 10\mu\text{F},\ L = 4.7\mu\text{H},\ unless otherwise specified.})$

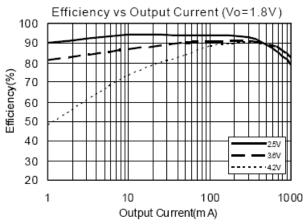
Symbol	Parameter	Test Conditions		Min	Тур	Max	Unit
Vin	Input Voltage Range	-		2.5	-	5.5	V
V _{FB}	Regulated Feedback Voltage	-		0.588	0.6	0.612	V
ΔV_{FB}	Reference Voltage Line Regulation	-		-	0.3	-	%/V
Vo	Regulated Output Voltage Accuracy	Io = 100mA		-3	-	+3	%
Ipk	Peak Inductor Current	V _{IN} = 3V, V _{FB} = 0.5	V or Vo = 90%	-	1.5	-	Α
LNR	Output Voltage Line Regulation	V _{IN} = 2.5V to 5v, I _O	= 10mA	-	0.2	0.5	%/V
LDR	Output Voltage Load Regulation	Io = 800mA		-	0.5	1.5	%
lq	Quiescent Current	No Load		-	40	70	μA
I _{SD}	Shutdown Current	V _{EN} = 0V		-	-	1	μΑ
fosc	Oscillator Fraguency	V _O = 100%		1.2	1.5	1.8	MHz
	Oscillator Frequency	$V_{FB} = 0V$ or $V_O = 0V$		-	500	-	kHz
RDS(ON)	Drain-Source On-State Resistance	lps = 100mA	P MOSFET	-	0.3	0.45	Ω
	Dialii-Source Oil-State Resistance	N MOS	N MOSFET	-	0.35	0.5	Ω
ILSW	SW Leakage Current	-		-	±0.01	1	μA
η	High Efficiency	-		-	96	-	%
VEH	EN Threshold High	-		1.5	-	-	V
VEL	EN Threshold Low	-		-	-	0.3	V
len	EN Leakage Current	-		-	±0.01	-	μΑ
OTP	Over Temperature Protection	erature Protection -		-	+150	-	°C
OTH	OTP Hysteresis	-	-		+30	-	°C

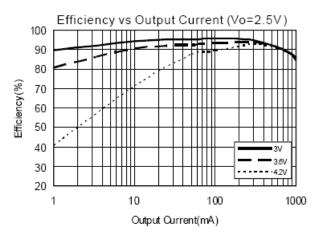


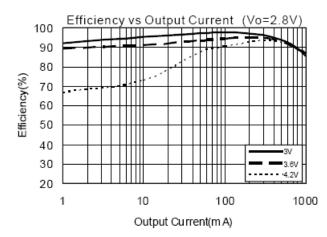
$\textbf{Typical Performance Characteristics} \ (@T_A = +25 ^{\circ}\text{C}, \ C_{\text{IN}} = 10 \mu\text{F}, \ C_{\text{O}} = 10 \mu\text{F}, \ L = 4.7 \mu\text{H}, \ unless \ otherwise \ specified.})$

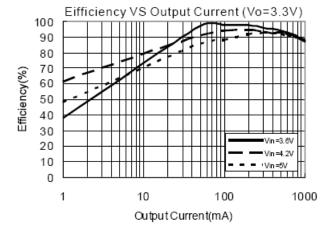






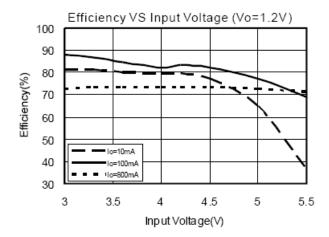


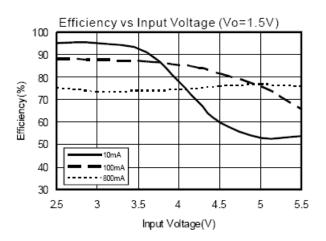


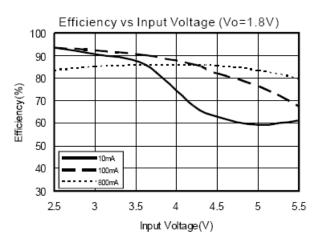


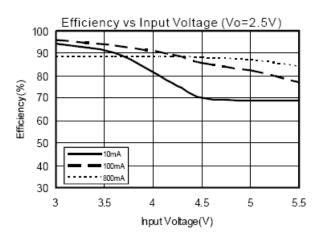


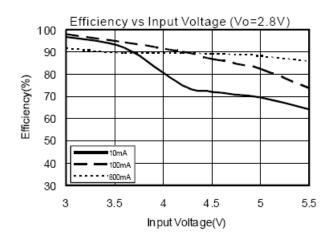
$\textbf{Typical Performance Characteristics} \ (\texttt{Cont.}) \ (@T_{\texttt{A}} = +25^{\circ}\texttt{C}, \ \texttt{C}_{\texttt{IN}} = 10 \mu \texttt{F}, \ \texttt{C}_{\texttt{O}} = 10 \mu \texttt{F}, \ \texttt{L} = 4.7 \mu \texttt{H}, \ unless \ otherwise \ specified.})$

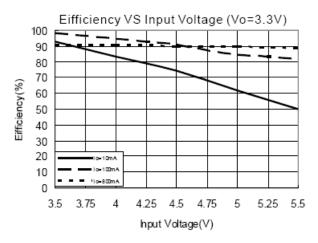






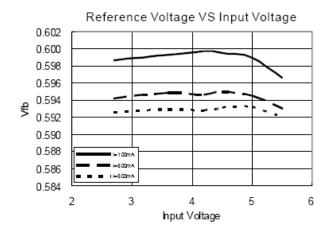


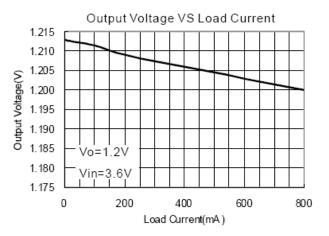


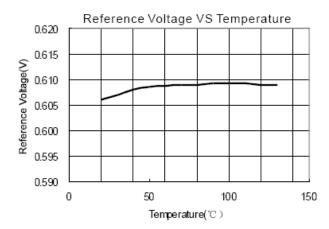


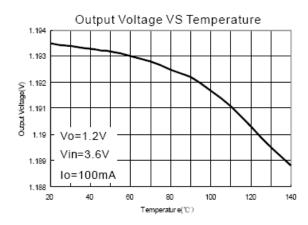


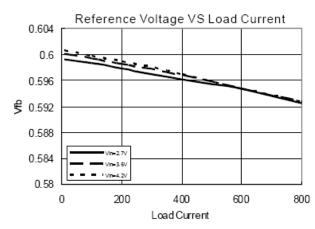
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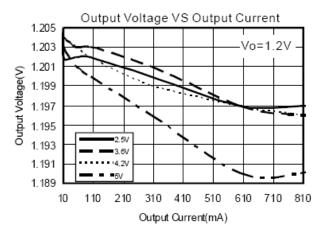






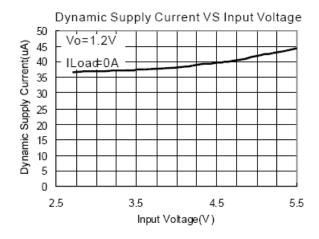


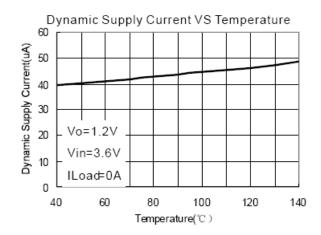


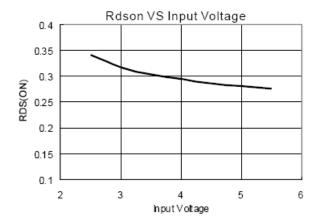


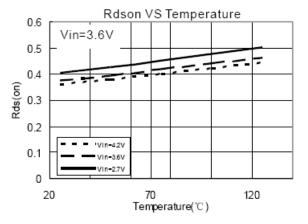


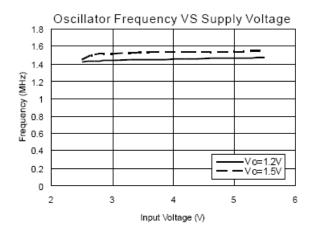
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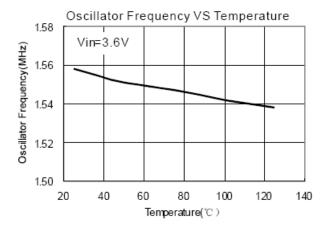






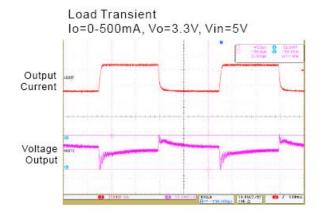


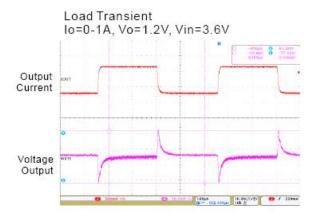


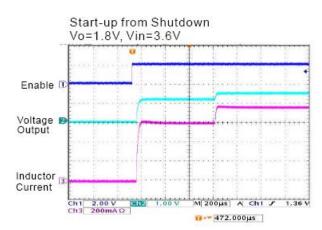




Typical Performance Characteristics (Cont.) (@TA = +25°C, C_{IN} = 10 μ F, C_{O} = 10 μ F, L = 4.7 μ H, unless otherwise specified.)









Application Information

The basic PAM2312 application circuit is shown in Page 1. External component selection is determined by the load requirement, selecting L first and then CIN and COUT.

Inductor Selection

For most applications, the value of the inductor will fall in the range of 1µH to 4.7µH. Its value is chosen based on the desired ripple current. Large value inductors lower ripple current and small value inductors result in higher ripple currents. Higher VIN or VOUT also increases the ripple current as shown in Equation 1. A reasonable starting point for setting ripple current is ΔI_L = 400mA (40% of 1A).

$$\Delta I_{L} = \frac{1}{(f)(L)} V_{OUT} \left(1 - \frac{V_{OUT}}{V_{IN}} \right)$$
 Equation (1)

The DC current rating of the inductor should be at least equal to the maximum load current plus half the ripple current to prevent core saturation. Thus, a 1.4A rated inductor should be enough for most applications (1A + 400mA). For better efficiency, choose a low DC-resistance inductor.

Vo	1.2V	1.5V	1.8V	2.5V	3.3V
L	2.2µH	2.2µH	4.7µH	4.7µH	4.7µH

CIN and COUT Selection

In continuous mode, the source current of the top MOSFET is a square wave of duty cycle Vout/Vin. To prevent large voltage transients, a low ESR input capacitor sized for the maximum RMS current must be used. The maximum RMS capacitor current is given by:

$$C_{IN}$$
 required $I_{RMS} \cong I_{OMAX} \frac{\left[V_{OUT} \left(V_{IN} - V_{OUT}\right)\right]^{1/2}}{V_{IN}}$

This formula has a maximum at V_{IN} = 2V_{OUT}, where I_{RMS} = I_{OUT}/2. This simple worst-case condition is commonly used for design because even significant deviations do not offer much relief. Note that the capacitor manufacturer's ripple current ratings are often based on 2000 hours of life. This makes it advisable to further derate the capacitor, or choose a capacitor rated at a higher temperature than required. Consult the manufacturer if there is any question.

The selection of C_{OUT} is driven by the required effective series resistance (ESR).

Typically, once the ESR requirement for Cout has been met, the RMS current rating generally far exceeds the IRIPPLE (P-P) requirement. The output ripple ΔV_{OUT} is determined by:

$$\Delta V_{OUT} \approx \Delta I_{L} \bigg(\text{ESR} +$$

Where f = operating frequency, CouT = output capacitance and ∆IL = ripple current in the inductor. For a fixed output voltage, the output ripple is highest at maximum input voltage since ∆I_L increases with input voltage.

Using Ceramic Input and Output Capacitors

Higher values, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. Using ceramic capacitors can achieve very low output ripple and small circuit size.

When choosing the input and output ceramic capacitors, choose the X5R or X7R dielectric formulations. These dielectrics have the best temperature and voltage characteristics of all the ceramics for a given value and size.

Thermal Consideration

Thermal protection limits power dissipation in the PAM2312. When the junction temperature exceeds +150°C, the OTP (Over Temperature Protection) starts the thermal shutdown and turns the pass transistor off. The pass transistor resumes operation after the junction temperature drops below +120°C.

For continuous operation, the junction temperature should be maintained below +125°C. The power dissipation is defined as:

$$P_{D} = I_{O}^{2} \frac{V_{O} R_{DS(ON)H} + (V_{IN} - V_{O}) R_{DS(ON)L}}{V_{IN}} + (t_{SW} F_{S} I_{O} + I_{Q}) V_{IN}$$

Iq is the step-down converter quiescent current. The term tsw is used to estimate the full load step-down converter switching losses.

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March 2020



Application Information (Cont.)

For the condition where the step-down converter is in dropout at 100% duty cycle, the total device dissipation reduces to:

$$P_D = I_O^2 R_{DS(ON)H} + I_O V_{IN}$$

Since RDS(ON), quiescent current, and switching losses all vary with input voltage, the total losses should be investigated over the complete input voltage range. The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surrounding airflow and temperature difference between junction and ambient. The maximum power dissipation can be calculated by the following formula:

$$P_D = \frac{T_{J(MAX)} - T_A}{\theta_{JA}}$$

Where T_{J(MAX)} is the maximum allowable junction temperature +125°C. T_A is the ambient temperature and θ_{JA} is the thermal resistance from the junction to the ambient. Based on the standard JEDEC for a two layers thermal test board, the thermal resistance θ_{JA} of TSOT25 package is 250°C/W. The maximum power dissipation at T_A = +25°C can be calculated by following formula:

$$P_D = (125^{\circ}C - 25^{\circ}C) / 250^{\circ}C/W = 0.4W$$

Setting the Output Voltage

The internal reference is 0.6V (Typical). The output voltage is calculated as below:

The output voltage is given by Table 1.

$$V_O = 0.6x \left(1 + \frac{R1}{R2}\right)$$

Table 1: Resistor selection for output voltage setting.

Vo	R1	R2
1.2V	100k	100k
1.5V	150k	100k
1.8V	200k	100k
2.5V	380k	120k
3.3V	540k	120k

100% Duty Cycle Operation

As the input voltage approaches the output voltage, the converter turns the P-channel transistor continuously on. In this mode the output voltage is equal to the input voltage minus the voltage drop across the P-Channel transistor:

$$V_{OUT} = V_{IN} - I_{LOAD} (R_{DSON} + R_L)$$

where RDS(ON) = P-Channel switch ON resistance, ILOAD = Output Current, RL = Inductor DC Resistance

UVLO and Soft-Start

The reference and the circuit remain reset until the V_{IN} crosses its UVLO threshold. The PAM2312 has an internal soft-start circuit that limits the in-rush current during start-up. This prevents possible voltage drops of the input voltage and eliminates the output voltage overshoot. The softstart acts as a digital circuit to increase the switch current in several steps to the P-channel current limit (1500mA).

Short Circuit Protection

The switch peak current is limited cycle-by-cycle to a typical value of 1500mA. In the event of an output voltage short circuit, the device operates with a frequency of 500kHz and minimum duty cycle, therefore the average input current is typically 200mA.

Thermal Shutdown

When the die temperature exceeds +150°C, a reset occurs and the reset remains until the temperature decrease to +120°C, at which time the circuit can be restarted.

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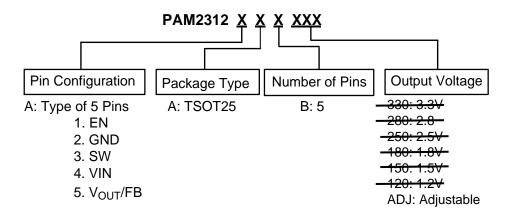
Application Information (Cont.)

PCB Layout Check List

When laying out the printed circuit board, the following checklist should be used to ensure proper operation of the PAM2312. These items are also illustrated graphically in Figure 1. Check the following in your layout:

- 1. The power traces, consisting of the GND trace, the SW trace and the V_{IN} trace should be kept short, direct and wide.
- 2. Does the VFB pin connect directly to the feedback resistors? The resistive divider R1/R2 must be connected between the (+) plate of Cout and ground.
- 3. Does the (+) plate of CIN connect to VIN as closely as possible? This capacitor provides the AC current to the internal power MOSFETs.
- 4. Keep the switching node, SW, away from the sensitive VFB node.
- 5. Keep the (-) plates of CIN and COUT as close as possible.

Ordering Information

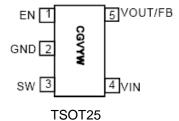


Part Number	Output Voltage	Package	Tape and Reel
	(V)	(Note 5)	Quantity
PAM2312AABADJ	ADJ	TSOT25	3000

Note: 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Top View



CG: Product Code of PAM2312

V: Output Voltage Y: Year

W: Week

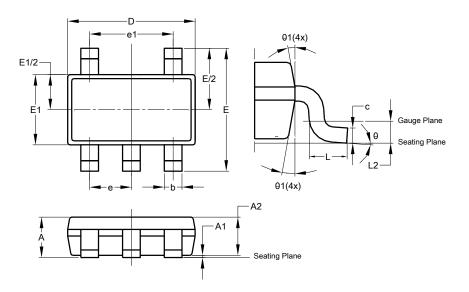
X: Internal Code



Package Outline Dimensions (All dimensions in mm.)

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT25

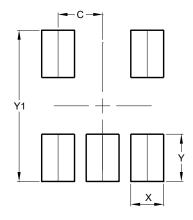


TSOT25					
Dim	Min Max Typ				
Α	-	1.00	-		
A 1	0.01	0.10	-		
A2	0.84	0.90	-		
b	0.30	0.45	-		
C	0.12	0.12 0.20 -			
D	2.90				
Е	2		2.80		
E1	1.60				
е	(0.95 BS	C		
e1	·	1.90 BS	C		
L	0.30 0.50 -		-		
L2	0.25 BSC				
θ	0°	8°	4°		
θ1	4° 12° -				
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT25



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3.199



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